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**(54) MANUFACTURE OF SEMICONDUCTOR SUPERLATTICE**

(57) Abstract:

**PURPOSE:** To form a Ge layer and an Si layer or a Ge-Si layer and an Si layer on an Si substrate, and also to put a hetero-epitaxial growth method, in which excellent crystal quality and high growth speed can be obtained, into practical use.

**CONSTITUTION:** The title semiconductor superlattice

manufacturing method is the method with which a Ge layer and an Si layer or Ge-Si layer and an Si layer are epitaxially grown on an Si substrate by conducting a depressed CVD method under the atmosphere containing oxidizing impurity gas of 1000ppb or lower using GeH<sub>4</sub> and trisilane (Si<sub>3</sub>H<sub>8</sub>) as raw gas and also using H<sub>2</sub> or inert gas as carrier gas.

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